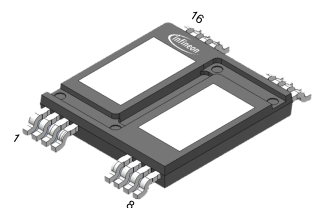


Final datasheet

CoolSiC™ 1200 V SiC MOSFET G2 : Silicon Carbide MOSFET with top side cooling and .XT technology

Features

- $V_{DS} = 1200\text{ V}$ at $T_{vj} = 25^\circ\text{C}$
- $I_{DC} = 11\text{ A}$ at $T_C = 100^\circ\text{C}$
- $R_{DS(on)} = 181\text{ m}\Omega$ at $V_{GS} = 18\text{ V}$, $T_{vj} = 25^\circ\text{C}$
- Internal layout optimized for fast switching
- Very low switching losses
- Overload operation up to $T_{vj} = 200^\circ\text{C}$
- Short circuit withstand time $2\text{ }\mu\text{s}$
- Benchmark gate threshold voltage, $V_{GS(th)} = 4.2\text{ V}$
- Robust against parasitic turn on, 0 V turn-off gate voltage can be applied
- Robust body diode for hard commutation
- .XT interconnection technology for best-in-class thermal performance
- Suitable Infineon gate drivers can be found under <https://www.infineon.com/gdfinder>



Potential applications

- String inverter
- EV Charging
- DIN Rail & Rack Mount (Power Supply)
- Commercial & Industrial Lighting

Product validation

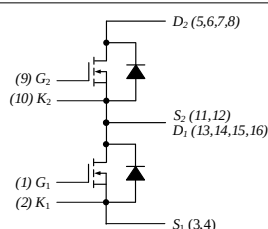
- Qualified for industrial applications according to the relevant tests of JEDEC47/20/22

Description

Pin definition:

- 13-16 (5-8) & Case1(2) - D1(D2)
- 3,4 (11,12) - S1(S2)
- 2(10) - Kelvin sense K1(K2)
- 1(9) - G1(G2)

Note: the source and sense pins are not exchangeable, their exchange might lead to malfunction



Type	Package	Marking
IMSQ120R181M2HH	PG-HDSOP-16-U03	12M2H181



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1 Package

1 Package

Table 1 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Storage temperature	T_{stg}		-55		150	°C
Soldering temperature	T_{sold}	Reflow soldering (MSL2 according to JEDEC J-STD-020)			260	°C
Thermal resistance, junction-ambient	$R_{th(j-a)}$				62	K/W
MOSFET/body diode thermal resistance, junction-case	$R_{th(j-c)}$			1.13	1.47	K/W

2 MOSFET

Table 2 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Drain-source voltage	V_{DSS}	$T_{vj} \geq 25\text{ °C}$		1200	V
Continuous DC drain current for $R_{th(j-c,max)}$, limited by $T_{vj(max)}$	I_{DDC}	$V_{GS}=18\text{ V}$	$T_c = 25\text{ °C}$	15.4	A
			$T_c = 100\text{ °C}$	11	
Peak drain current, t_p limited by $T_{vj(max)}$ ¹⁾	I_{DM}	$V_{GS}=18\text{ V}$		55	A
Gate-source voltage, max. transient voltage	V_{GS}	$t_p \leq 0.5\text{ }\mu\text{s}$, $D < 0.01$		-10/25	V
Gate-source voltage, max. static voltage ²⁾	V_{GS}			-7/23	V
Avalanche energy, single pulse	E_{AS}	$I_D = 3.8\text{ A}$, $V_{DD} = 50\text{ V}$, $L = 6.6\text{ mH}$, $T_{vj(start)} = 25\text{ °C}$		48	mJ
Avalanche energy, repetitive	E_{AR}	$I_D = 3.8\text{ A}$, $V_{DD} = 50\text{ V}$, $L = 33.2\text{ }\mu\text{H}$, $T_{vj(start)} = 25\text{ °C}$		0.24	mJ
Short-circuit withstand time	t_{SC}	$V_{DD} \leq 800\text{ V}$, $V_{DS,peak} < 1200\text{ V}$, $V_{GS(on)} = 15\text{ V}$, $T_{vj(start)} = 25\text{ °C}$		2	μs
Power dissipation, limited by $T_{vj(max)}$	P_{tot}		$T_c = 25\text{ °C}$	102	W
			$T_c = 100\text{ °C}$	51	

1) Verified by design.

2) The maximum gate-source voltage in the application design should be in accordance to IPC-9592B.

Table 3 Recommended values

Parameter	Symbol	Note or test condition	Values	Unit
Recommended turn-on gate voltage	$V_{GS(on)}$		15...18	V
Recommended turn-off gate voltage	$V_{GS(off)}$		-5...0	V

Table 4 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Drain-source on-state resistance	$R_{DS(on)}$	$I_D = 3.8 \text{ A}$		$T_{vj} = 25 \text{ °C}, V_{GS(on)} = 18 \text{ V}$	181	mΩ
				$T_{vj} = 150 \text{ °C}, V_{GS(on)} = 18 \text{ V}$	370	
				$T_{vj} = 175 \text{ °C}, V_{GS(on)} = 18 \text{ V}$	430	
				$T_{vj} = 25 \text{ °C}, V_{GS(on)} = 15 \text{ V}$	227	
Gate-source threshold voltage	$V_{GS(th)}$	$I_D = 1.2 \text{ mA}, V_{DS} = V_{GS}$ (tested after 1 ms pulse at $V_{GS} = 20 \text{ V}$)	3.5	$T_{vj} = 25 \text{ °C}$	4.2	V
				$T_{vj} = 175 \text{ °C}$	3.2	
Zero gate-voltage drain current	I_{DSS}	$V_{DS} = 1200 \text{ V}, V_{GS} = 0 \text{ V}$		$T_{vj} = 25 \text{ °C}$	30	μA
				$T_{vj} = 175 \text{ °C}$	0.56	
Gate leakage current	I_{GSS}	$V_{DS} = 0 \text{ V}$		$V_{GS} = 23 \text{ V}$	120	nA
				$V_{GS} = -10 \text{ V}$	-120	
Forward transconductance	g_{fs}	$I_D = 3.8 \text{ A}, V_{DS} = 20 \text{ V}$		2.5		S
Internal gate resistance	$R_{G,int}$	$f = 1 \text{ MHz}, V_{AC} = 25 \text{ mV}$		8.5		Ω
Input capacitance	C_{iss}	$V_{DS} = 800 \text{ V}, V_{GS} = 0 \text{ V}, f = 100 \text{ kHz}, V_{AC} = 25 \text{ mV}$		350		pF
Output capacitance	C_{oss}	$V_{DS} = 800 \text{ V}, V_{GS} = 0 \text{ V}, f = 100 \text{ kHz}, V_{AC} = 25 \text{ mV}$		12		pF
Reverse transfer capacitance	C_{rss}	$V_{DS} = 800 \text{ V}, V_{GS} = 0 \text{ V}, f = 100 \text{ kHz}, V_{AC} = 25 \text{ mV}$		1		pF
C_{oss} stored energy	E_{oss}	Calculated based on $C_{oss} = f(V_{DD})$		5		μJ
Output charge	Q_{oss}	Calculated based on $C_{oss} = f(V_{DD})$		18.9		nC
Effective output capacitance, energy related	$C_{o(er)}$	$V_{DS} = 0...800 \text{ V}, V_{GS} = 0 \text{ V},$ Calculated based on E_{oss}		15.6		pF
Effective output capacitance, time related	$C_{o(tr)}$	$I_D = \text{constant}, V_{DS} = 0...800 \text{ V}, V_{GS} = 0 \text{ V},$ Calculated based on Q_{oss}		23.6		pF
Total gate charge	Q_G	$V_{DD} = 800 \text{ V}, I_D = 3.8 \text{ A}, V_{GS} = 0/18 \text{ V}, \text{turn-on pulse}$		11		nC

(table continues...)

Table 4 (continued) **Characteristic values**

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Plateau gate charge	$Q_{GS(pl)}$	$V_{DD} = 800 \text{ V}$, $I_D = 3.8 \text{ A}$, $V_{GS} = 0/18 \text{ V}$, turn-on pulse		2.8		nC
Gate-drain charge	Q_{GD}	$V_{DD} = 800 \text{ V}$, $I_D = 3.8 \text{ A}$, $V_{GS} = 0/18 \text{ V}$, turn-on pulse		2.6		nC
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 800 \text{ V}$, $I_D = 3.8 \text{ A}$, $V_{GS} = 0/18 \text{ V}$, $R_{G,ext} = 2.3 \Omega$, $L_\sigma = 9 \text{ nH}$, diode: body diode at $V_{GS} = 0 \text{ V}$	$T_{vj} = 25 \text{ }^\circ\text{C}$	2.6		ns
			$T_{vj} = 175 \text{ }^\circ\text{C}$	1.9		
Rise time	t_r	$V_{DD} = 800 \text{ V}$, $I_D = 3.8 \text{ A}$, $V_{GS} = 0/18 \text{ V}$, $R_{G,ext} = 2.3 \Omega$, $L_\sigma = 9 \text{ nH}$, diode: body diode at $V_{GS} = 0 \text{ V}$	$T_{vj} = 25 \text{ }^\circ\text{C}$	1.4		ns
			$T_{vj} = 175 \text{ }^\circ\text{C}$	1.3		
Turn-off delay time	$t_{d(off)}$	$V_{DD} = 800 \text{ V}$, $I_D = 3.8 \text{ A}$, $V_{GS} = 0/18 \text{ V}$, $R_{G,ext} = 2.3 \Omega$, $L_\sigma = 9 \text{ nH}$, diode: body diode at $V_{GS} = 0 \text{ V}$	$T_{vj} = 25 \text{ }^\circ\text{C}$	5.1		ns
			$T_{vj} = 175 \text{ }^\circ\text{C}$	6		
Fall time	t_f	$V_{DD} = 800 \text{ V}$, $I_D = 3.8 \text{ A}$, $V_{GS} = 0/18 \text{ V}$, $R_{G,ext} = 2.3 \Omega$, $L_\sigma = 9 \text{ nH}$, diode: body diode at $V_{GS} = 0 \text{ V}$	$T_{vj} = 25 \text{ }^\circ\text{C}$	1.9		ns
			$T_{vj} = 175 \text{ }^\circ\text{C}$	2.3		
Turn-on energy	E_{on}	$V_{DD} = 800 \text{ V}$, $I_D = 3.8 \text{ A}$, $V_{GS} = 0/18 \text{ V}$, $R_{G,ext} = 2.3 \Omega$, $L_\sigma = 9 \text{ nH}$, diode: body diode at $V_{GS} = 0 \text{ V}$	$T_{vj} = 25 \text{ }^\circ\text{C}$	19.8		μJ
			$T_{vj} = 175 \text{ }^\circ\text{C}$	52.1		
Turn-off energy	E_{off}	$V_{DD} = 800 \text{ V}$, $I_D = 3.8 \text{ A}$, $V_{GS} = 0/18 \text{ V}$, $R_{G,ext} = 2.3 \Omega$, $L_\sigma = 9 \text{ nH}$, diode: body diode at $V_{GS} = 0 \text{ V}$	$T_{vj} = 25 \text{ }^\circ\text{C}$	5		μJ
			$T_{vj} = 175 \text{ }^\circ\text{C}$	5		
Total switching energy ¹⁾	E_{tot}	$V_{DD} = 800 \text{ V}$, $I_D = 3.8 \text{ A}$, $V_{GS} = 0/18 \text{ V}$, $R_{G,ext} = 2.3 \Omega$, $L_\sigma = 9 \text{ nH}$, diode: body diode at $V_{GS} = 0 \text{ V}$	$T_{vj} = 25 \text{ }^\circ\text{C}$	40		μJ
			$T_{vj} = 175 \text{ }^\circ\text{C}$	90		

(table continues...)

Table 4 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Turn-on energy at -5 V	E_{on}	$V_{DD} = 800 \text{ V}$, $I_D = 3.8 \text{ A}$, $V_{GS} = -5/18 \text{ V}$, $R_{G,ext} = 2.3 \Omega$, $L_\sigma = 9 \text{ nH}$, diode: body diode at $V_{GS} = -5 \text{ V}$	$T_{vj} = 25 \text{ }^\circ\text{C}$	19.8		μJ
			$T_{vj} = 175 \text{ }^\circ\text{C}$	53.5		
Turn-off energy at -5 V	E_{off}	$V_{DD} = 800 \text{ V}$, $I_D = 3.8 \text{ A}$, $V_{GS} = -5/18 \text{ V}$, $R_{G,ext} = 2.3 \Omega$, $L_\sigma = 9 \text{ nH}$, diode: body diode at $V_{GS} = -5 \text{ V}$	$T_{vj} = 25 \text{ }^\circ\text{C}$	5		μJ
			$T_{vj} = 175 \text{ }^\circ\text{C}$	5		
Total switching energy at -5 V ¹⁾	E_{tot}	$V_{DD} = 800 \text{ V}$, $I_D = 3.8 \text{ A}$, $V_{GS} = -5/18 \text{ V}$, $R_{G,ext} = 2.3 \Omega$, $L_\sigma = 9 \text{ nH}$, diode: body diode at $V_{GS} = -5 \text{ V}$	$T_{vj} = 25 \text{ }^\circ\text{C}$	35.8		μJ
			$T_{vj} = 175 \text{ }^\circ\text{C}$	95.5		
Virtual junction temperature	T_{vj}		-55		175	$^\circ\text{C}$
Virtual junction temperature	$T_{vj(over)}$	overload, cumulative max. 100 h ²⁾			200	$^\circ\text{C}$

1) including E_{fr}

2) up to 5000 cycles. Maximum ΔT limited to 100 K.

Note: The chip technology was characterized up to 200 kV/ μs . The measured dV/dt was limited by measurement test setup and package.

Characteristics at $T_{vj} = 25^\circ\text{C}$, unless otherwise specified.

3 Body diode (MOSFET)

Table 5 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Drain-source voltage	V_{DSS}	$T_{vj} \geq 25 \text{ }^\circ\text{C}$		1200	V
Continuous reverse drain current for $R_{th(j-c,max)}$, limited by $T_{vj(max)}$	I_{SDC}	$V_{GS} = 0 \text{ V}$	$T_c = 25 \text{ }^\circ\text{C}$	14.9	A
			$T_c = 100 \text{ }^\circ\text{C}$	9	
Peak reverse drain current, t_p limited by $T_{vj(max)}$	I_{SM}	$V_{GS} = 0 \text{ V}$		33	A

Table 6 Characteristic values

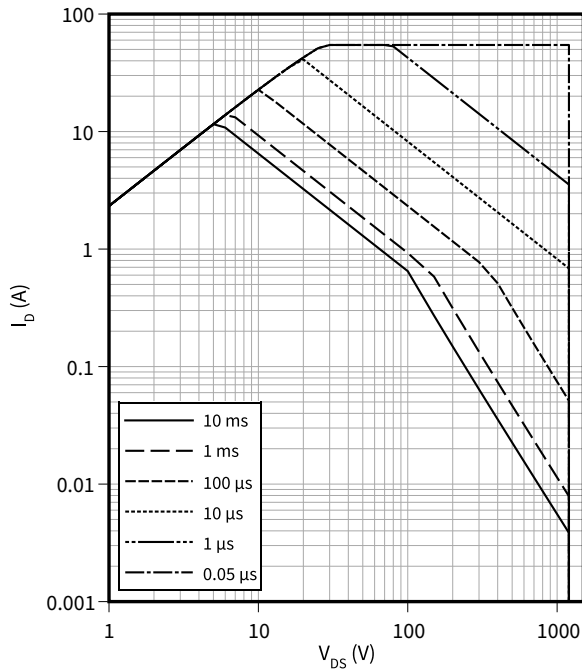
Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Drain-source reverse voltage	V_{SD}	$I_{SD} = 3.8 \text{ A}$, $V_{GS} = 0 \text{ V}$	$T_{vj} = 25 \text{ °C}$	4.2	5.5	V
			$T_{vj} = 100 \text{ °C}$	4.11		
			$T_{vj} = 175 \text{ °C}$	4.05		
MOSFET forward recovery charge	Q_{fr}	$V_{DD} = 800 \text{ V}$, $I_{SD} = 3.8 \text{ A}$, $V_{GS} = 0 \text{ V}$, $R_{G,ext} = 2.3 \text{ } \Omega$, Q_{fr} includes also Q_C	$T_{vj} = 25 \text{ °C}$	0.25		μC
			$T_{vj} = 175 \text{ °C}$	0.3		
MOSFET peak forward recovery current	I_{frm}	$V_{DD} = 800 \text{ V}$, $I_{SD} = 3.8 \text{ A}$, $V_{GS} = 0 \text{ V}$, $R_{G,ext} = 2.3 \text{ } \Omega$, Q_{fr} includes also Q_C	$T_{vj} = 25 \text{ °C}$	32		A
			$T_{vj} = 175 \text{ °C}$	41		
MOSFET forward recovery energy	E_{fr}	$V_{DD} = 800 \text{ V}$, $I_{SD} = 3.8 \text{ A}$, $V_{GS} = 0 \text{ V}$, $R_{G,ext} = 2.3 \text{ } \Omega$, Q_{fr} includes also Q_C	$T_{vj} = 25 \text{ °C}$	11		μJ
			$T_{vj} = 175 \text{ °C}$	36		
MOSFET forward recovery energy at -5 V	E_{fr}	$V_{DD} = 800 \text{ V}$, $I_{SD} = 3.8 \text{ A}$, $V_{GS} = -5 \text{ V}$, $R_{G,ext} = 2.3 \text{ } \Omega$, Q_{fr} includes also Q_C	$T_{vj} = 25 \text{ °C}$	11		μJ
			$T_{vj} = 175 \text{ °C}$	37		
Virtual junction temperature	T_{vj}		-55		175	$^{\circ}\text{C}$
Virtual junction temperature	$T_{vj(over)}$	overload, cumulative max. 100 h ¹⁾			200	$^{\circ}\text{C}$

1) up to 5000 cycles. Maximum ΔT limited to 100 K.

4 Characteristics diagrams

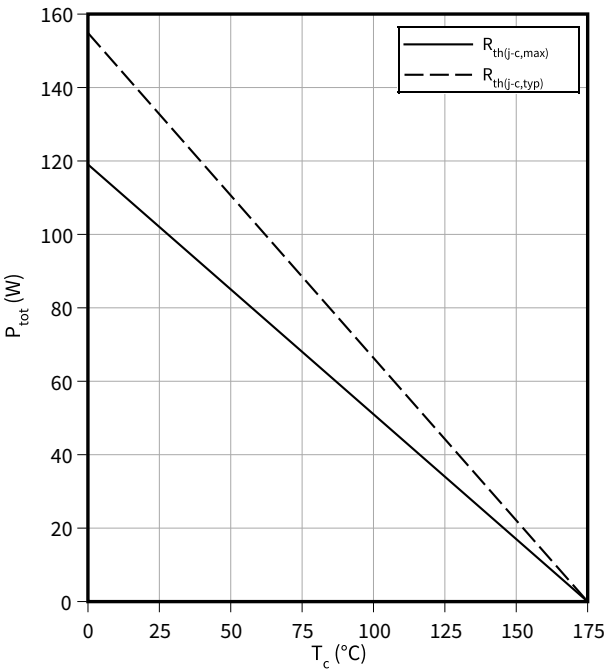
Safe operating area (SOA)

$I_D = f(V_{DS})$
 $T_{vj} \leq 175\text{ °C}, T_c = 25\text{ °C}$



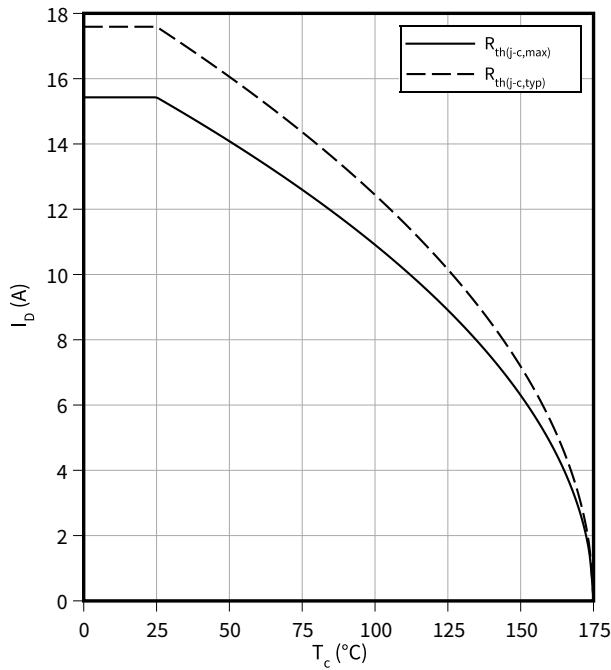
Power dissipation as a function of case temperature

$P_{tot} = f(T_c)$



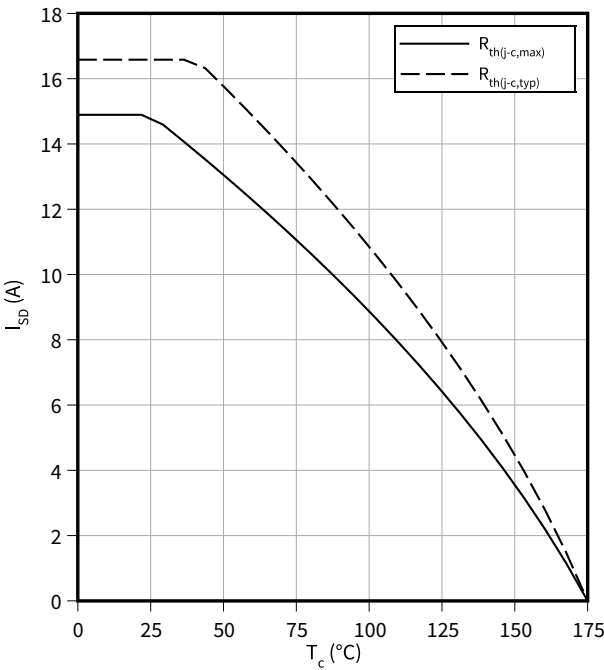
Maximum DC drain to source current as a function of case temperature limited by bond wire

$I_D = f(T_c)$



Maximum source to drain current as a function of case temperature limited by bond wire

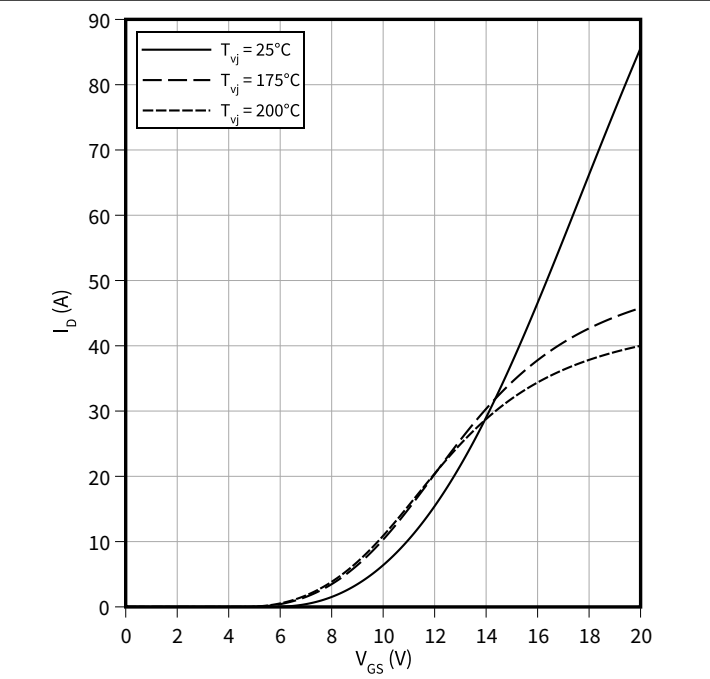
$I_{SD} = f(T_c)$
 $V_{GS} = 0\text{ V}$



4 Characteristics diagrams

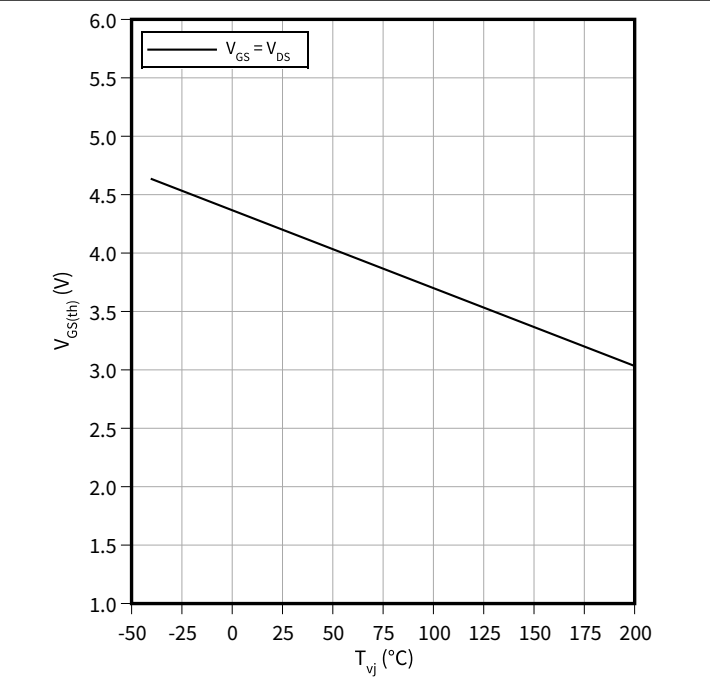
Typical transfer characteristic

$I_D = f(V_{GS})$
 $V_{DS} = 20\text{ V}$, $t_p = 20\text{ }\mu\text{s}$



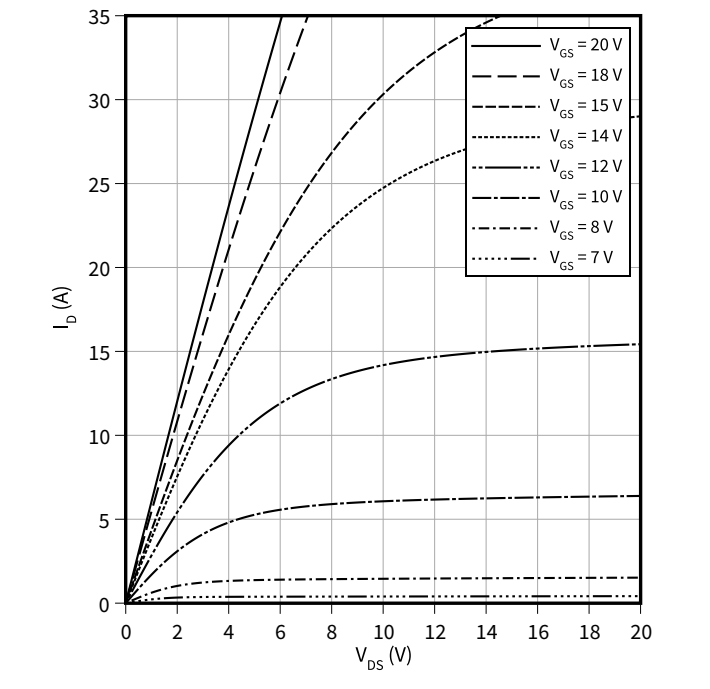
Typical gate-source threshold voltage as a function of junction temperature

$V_{GS(th)} = f(T_{vj})$
 $I_D = 1.2\text{ mA}$



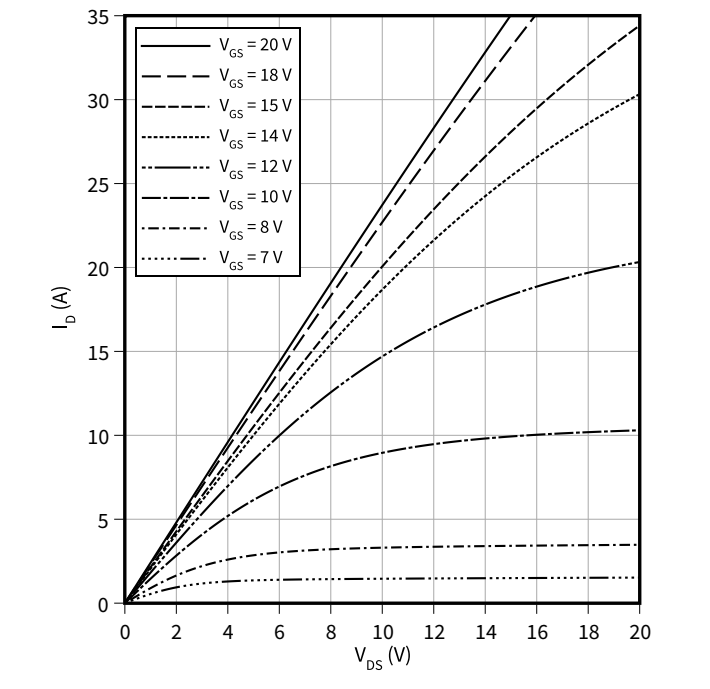
Typical output characteristic, V_{GS} as a parameter

$I_D = f(V_{DS})$
 $T_{vj} = 25\text{ }^\circ\text{C}$, $t_p = 20\text{ }\mu\text{s}$



Typical output characteristic, V_{GS} as a parameter

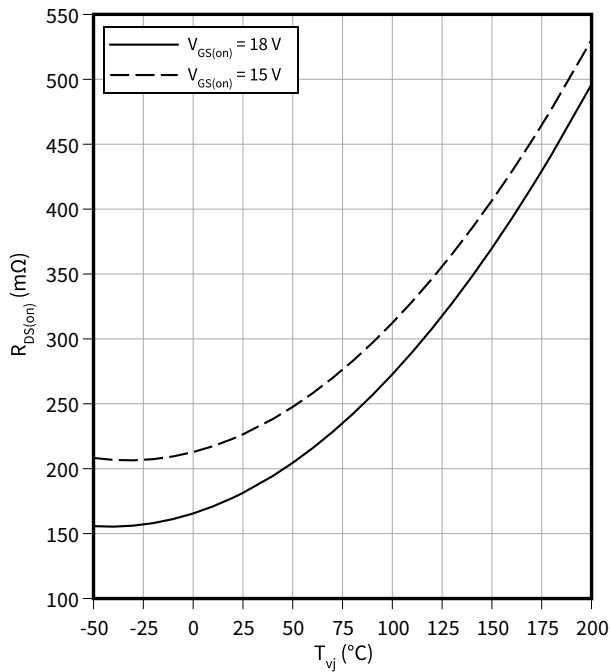
$I_D = f(V_{DS})$
 $T_{vj} = 175\text{ }^\circ\text{C}$, $t_p = 20\text{ }\mu\text{s}$



4 Characteristics diagrams

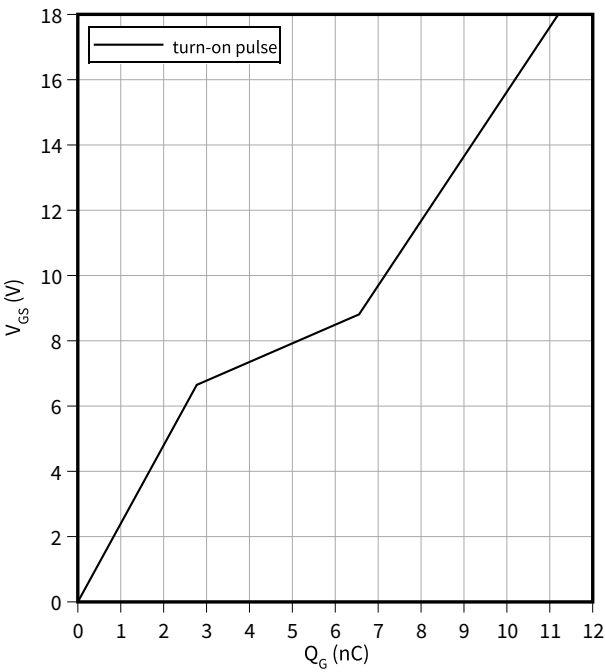
Typical on-state resistance as a function of junction temperature

$R_{DS(on)} = f(T_{vj})$
 $I_D = 3.8\text{ A}$



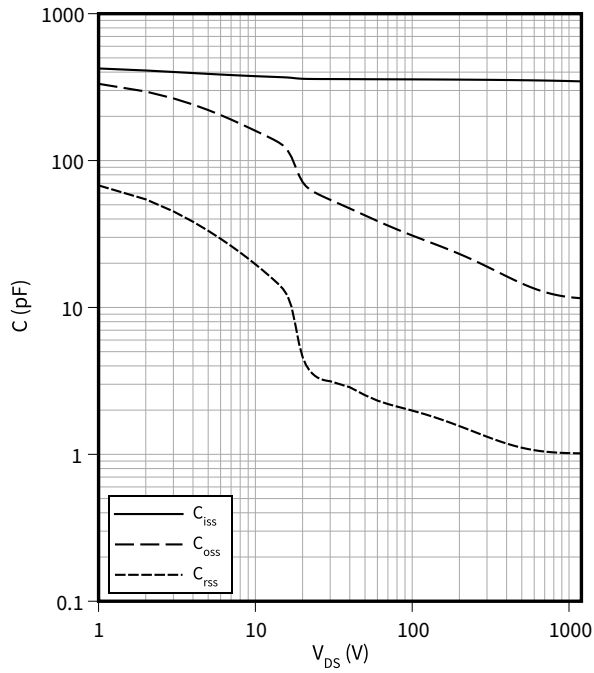
Typical gate charge

$V_{GS} = f(Q_G)$
 $I_D = 3.8\text{ A}, V_{DS} = 800\text{ V}$



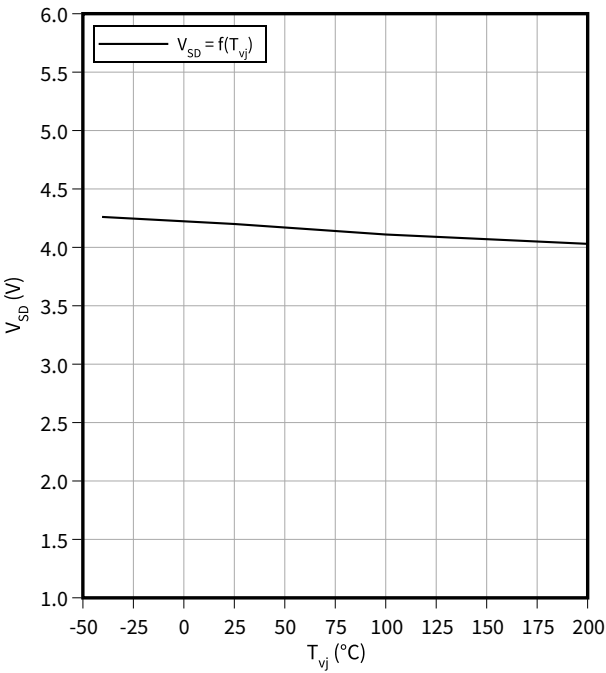
Typical capacitance as a function of drain-source voltage

$C = f(V_{DS})$
 $f = 100\text{ kHz}, V_{GS} = 0\text{ V}$



Typical reverse drain voltage as a function of junction temperature

$V_{SD} = f(T_{vj})$
 $I_{SD} = 3.8\text{ A}, V_{GS} = 0\text{ V}$

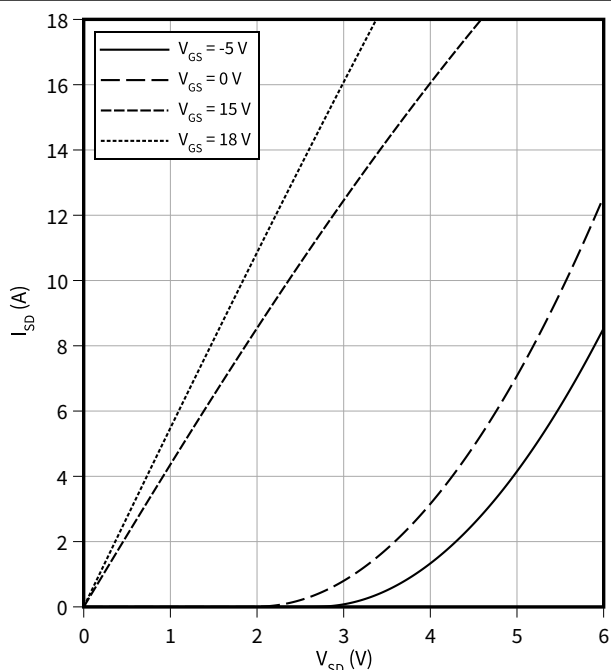


4 Characteristics diagrams

Typical reverse drain current as a function of reverse drain voltage, V_{GS} as a parameter

$$I_{SD} = f(V_{SD})$$

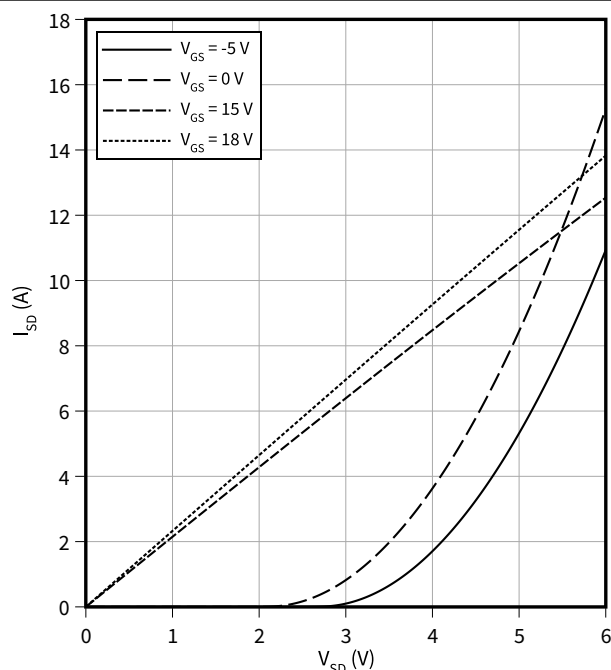
$T_{vj} = 25\text{ °C}$, $t_p = 20\text{ }\mu\text{s}$



Typical reverse drain current as a function of reverse drain voltage, V_{GS} as a parameter

$$I_{SD} = f(V_{SD})$$

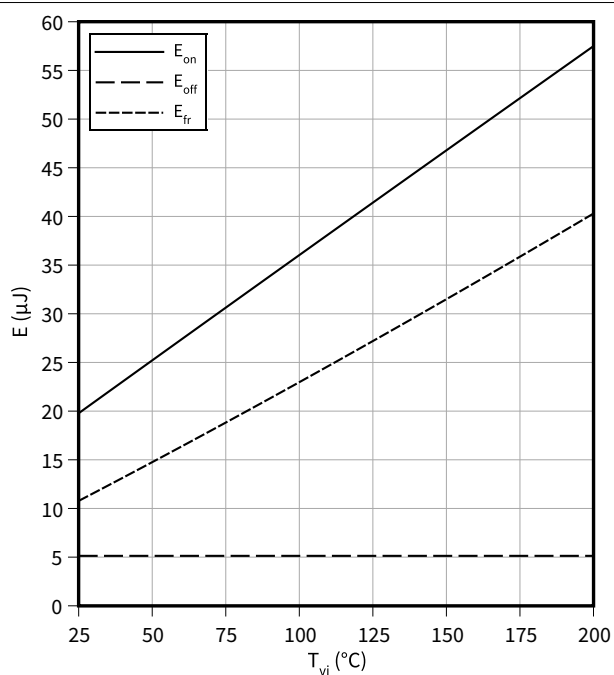
$T_{vj} = 175\text{ °C}$, $t_p = 20\text{ }\mu\text{s}$



Typical switching energy as a function of junction temperature, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = 0\text{ V}$

$$E = f(T_{vj})$$

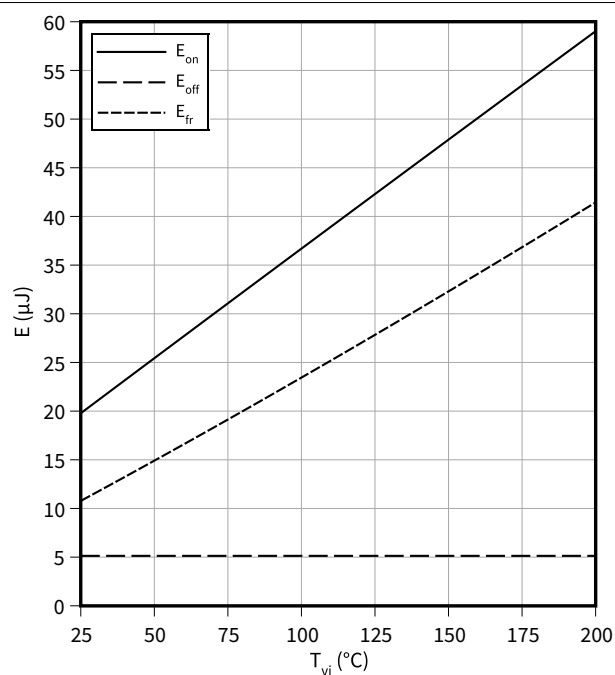
$V_{GS} = 0/18\text{ V}$, $I_D = 3.8\text{ A}$, $R_{G,ext} = 2.3\text{ }\Omega$, $V_{DD} = 800\text{ V}$



Typical switching energy as a function of junction temperature, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = -5\text{ V}$

$$E = f(T_{vj})$$

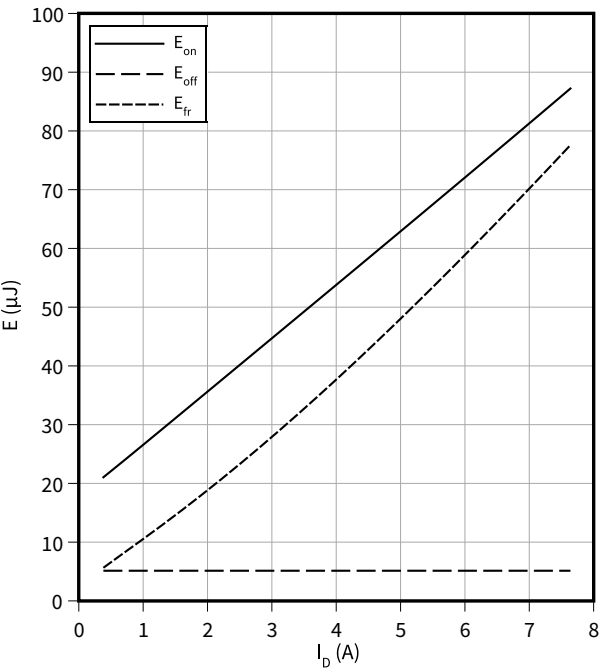
$V_{GS} = -5/18\text{ V}$, $I_D = 3.8\text{ A}$, $R_{G,ext} = 2.3\text{ }\Omega$, $V_{DD} = 800\text{ V}$



4 Characteristics diagrams

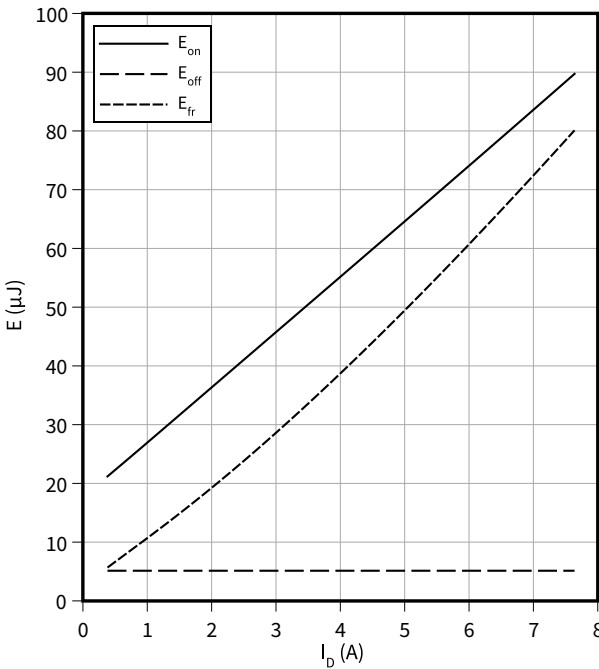
Typical switching energy as a function of drain current, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = 0\text{ V}$

$E = f(I_D)$
 $V_{GS} = 0/18\text{ V}$, $T_{vj} = 175\text{ °C}$, $R_{G,ext} = 2.3\text{ }\Omega$, $V_{DD} = 800\text{ V}$



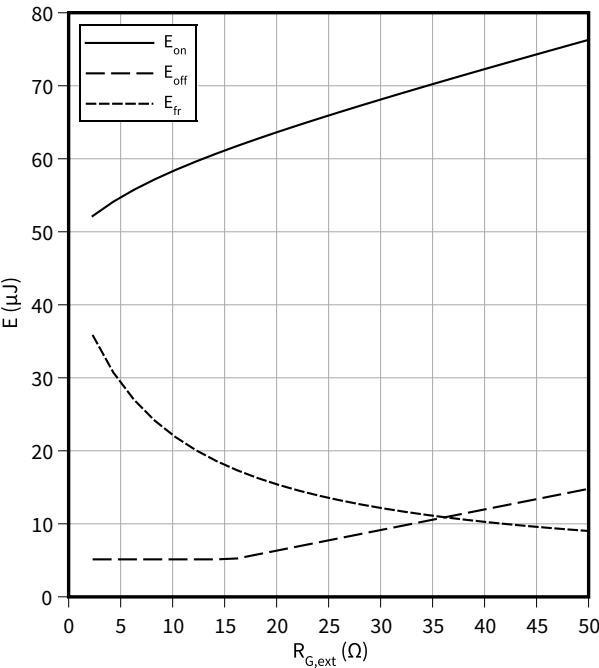
Typical switching energy as a function of drain current, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = -5\text{ V}$

$E = f(I_D)$
 $V_{GS} = -5/18\text{ V}$, $T_{vj} = 175\text{ °C}$, $R_{G,ext} = 2.3\text{ }\Omega$, $V_{DD} = 800\text{ V}$



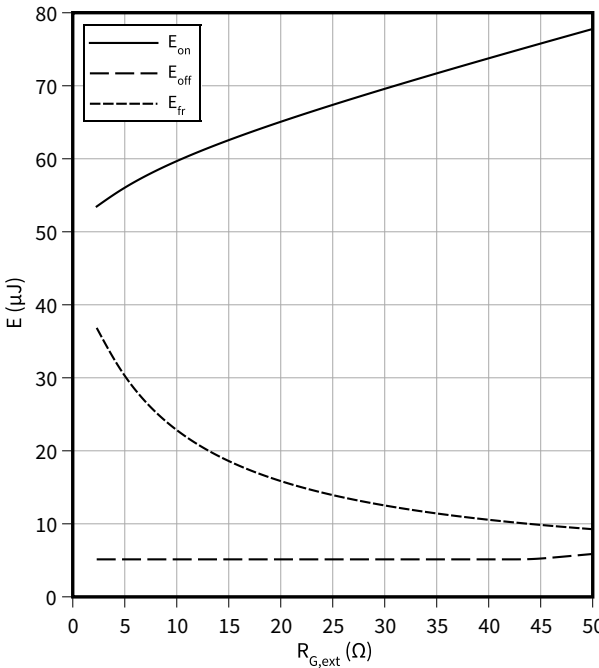
Typical switching energy as a function of gate resistance, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = 0\text{ V}$

$E = f(R_{G,ext})$
 $V_{GS} = 0/18\text{ V}$, $I_D = 3.8\text{ A}$, $T_{vj} = 175\text{ °C}$, $V_{DD} = 800\text{ V}$



Typical switching energy as a function of gate resistance, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = -5\text{ V}$

$E = f(R_{G,ext})$
 $V_{GS} = -5/18\text{ V}$, $I_D = 3.8\text{ A}$, $T_{vj} = 175\text{ °C}$, $V_{DD} = 800\text{ V}$

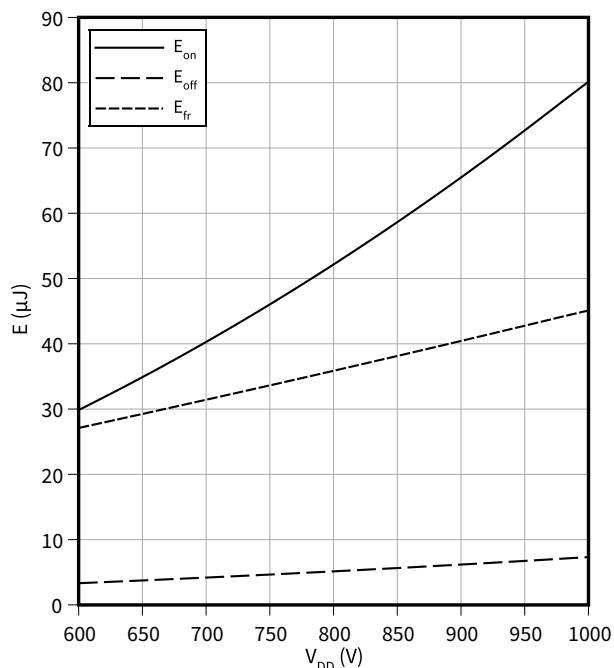


4 Characteristics diagrams

Typical switching energy as a function of DC link voltage, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = 0$ V

$$E = f(V_{DD})$$

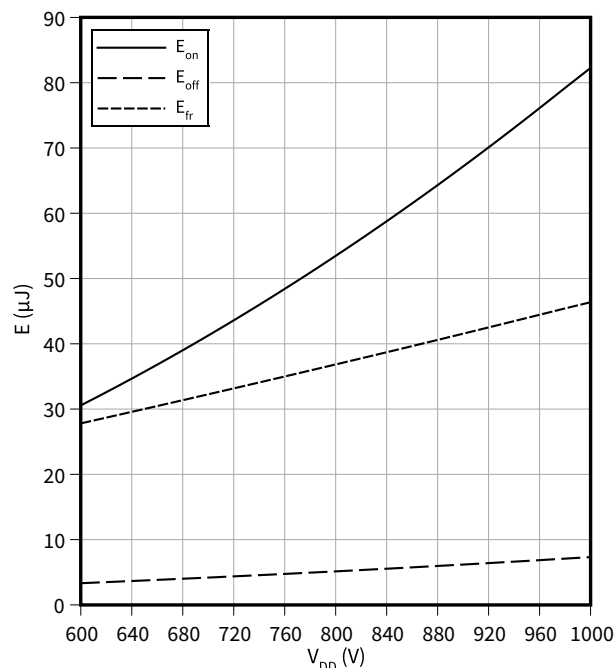
$V_{GS} = 0/18$ V, $I_D = 3.8$ A, $T_{vj} = 175$ °C, $R_{G,ext} = 2.3$ Ω



Typical switching energy as a function of DC link voltage, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = -5$ V

$$E = f(V_{DD})$$

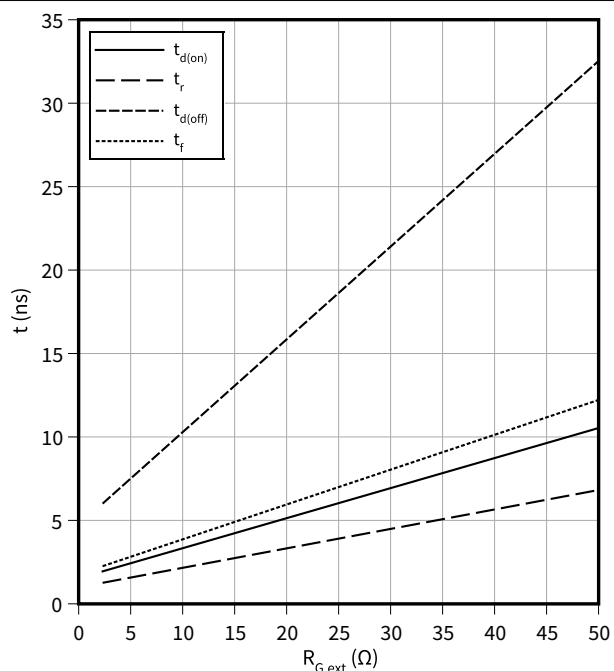
$V_{GS} = -5/18$ V, $I_D = 3.8$ A, $T_{vj} = 175$ °C, $R_{G,ext} = 2.3$ Ω



Typical switching times as a function of gate resistance, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = 0$ V

$$t = f(R_{G,ext})$$

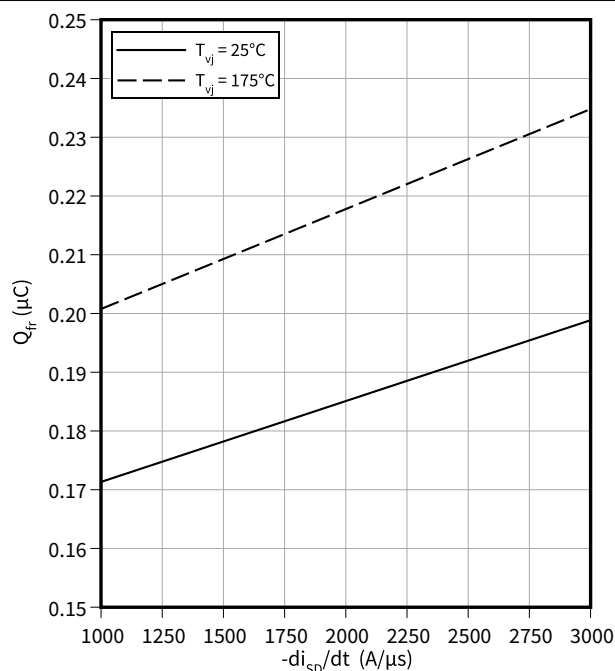
$V_{GS} = 0/18$ V, $I_D = 3.8$ A, $T_{vj} = 175$ °C, $V_{DD} = 800$ V



Typical reverse recovery charge as a function of reverse drain current slope, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = 0$ V

$$Q_{fr} = f(-di_{SD}/dt)$$

$V_{GS} = 0/18$ V, $I_{SD} = 3.8$ A, $V_{DD} = 800$ V



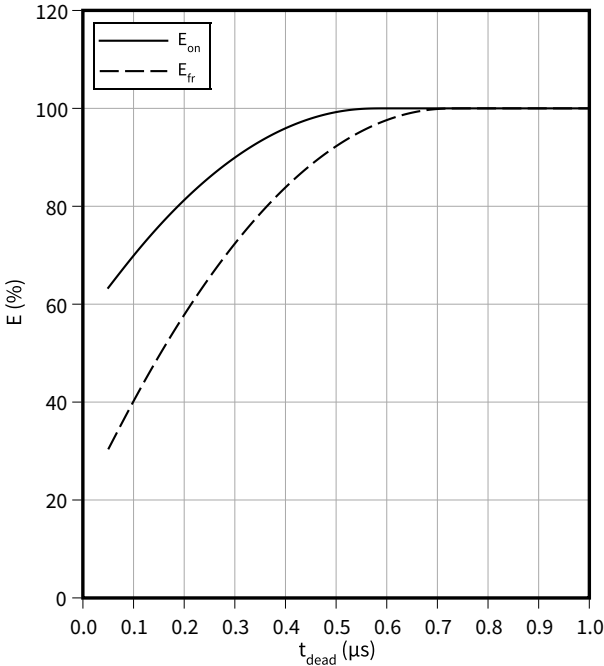
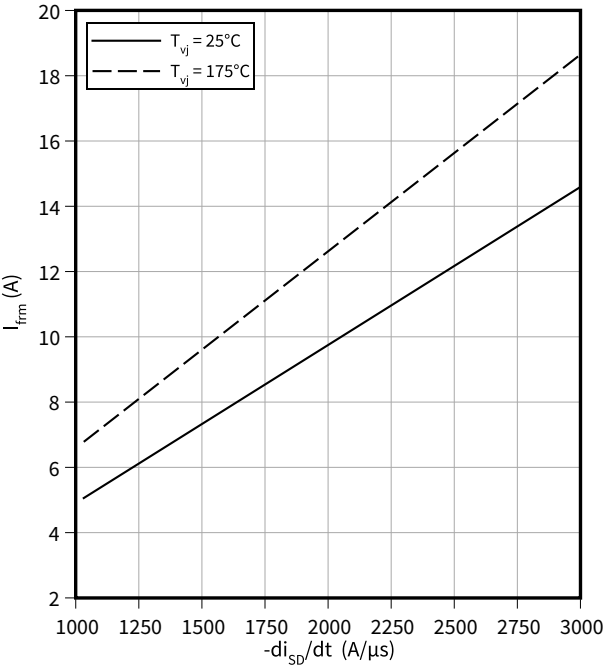
4 Characteristics diagrams

Typical reverse recovery current as a function of reverse drain current slope, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = 0\text{ V}$

$I_{frm} = f(-di_{SD}/dt)$
 $V_{GS} = 0/18\text{ V}, I_{SD} = 3.8\text{ A}, V_{DD} = 800\text{ V}$

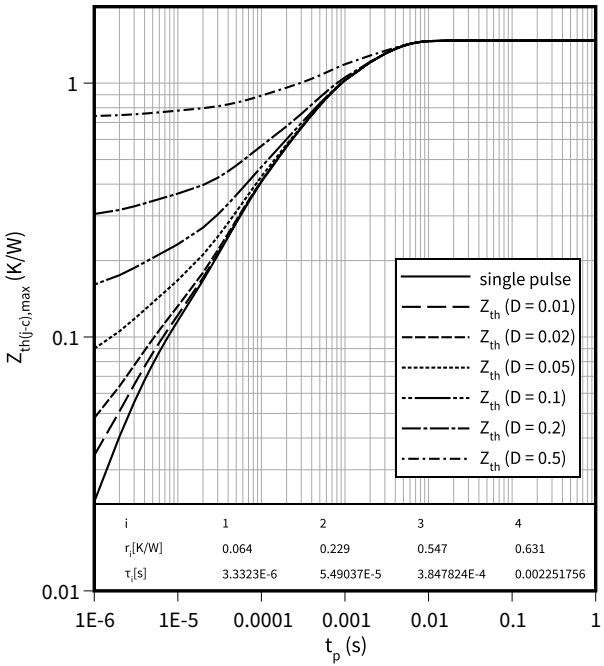
Typical switching energy as a function of dead time / blanking time, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = 0\text{ V}$

$E = f(t_{dead})$
 $V_{GS} = 0/18\text{ V}, I_D = 3.8\text{ A}, T_{vj} = 175\text{ °C}, R_{G,ext} = 2.3\text{ }\Omega$
 $V_{DD} = 800\text{ V}$



Max. transient thermal impedance (MOSFET/diode)

$Z_{th(j-c),max} = f(t_p)$
 $D = t_p/T$



5 Package outlines

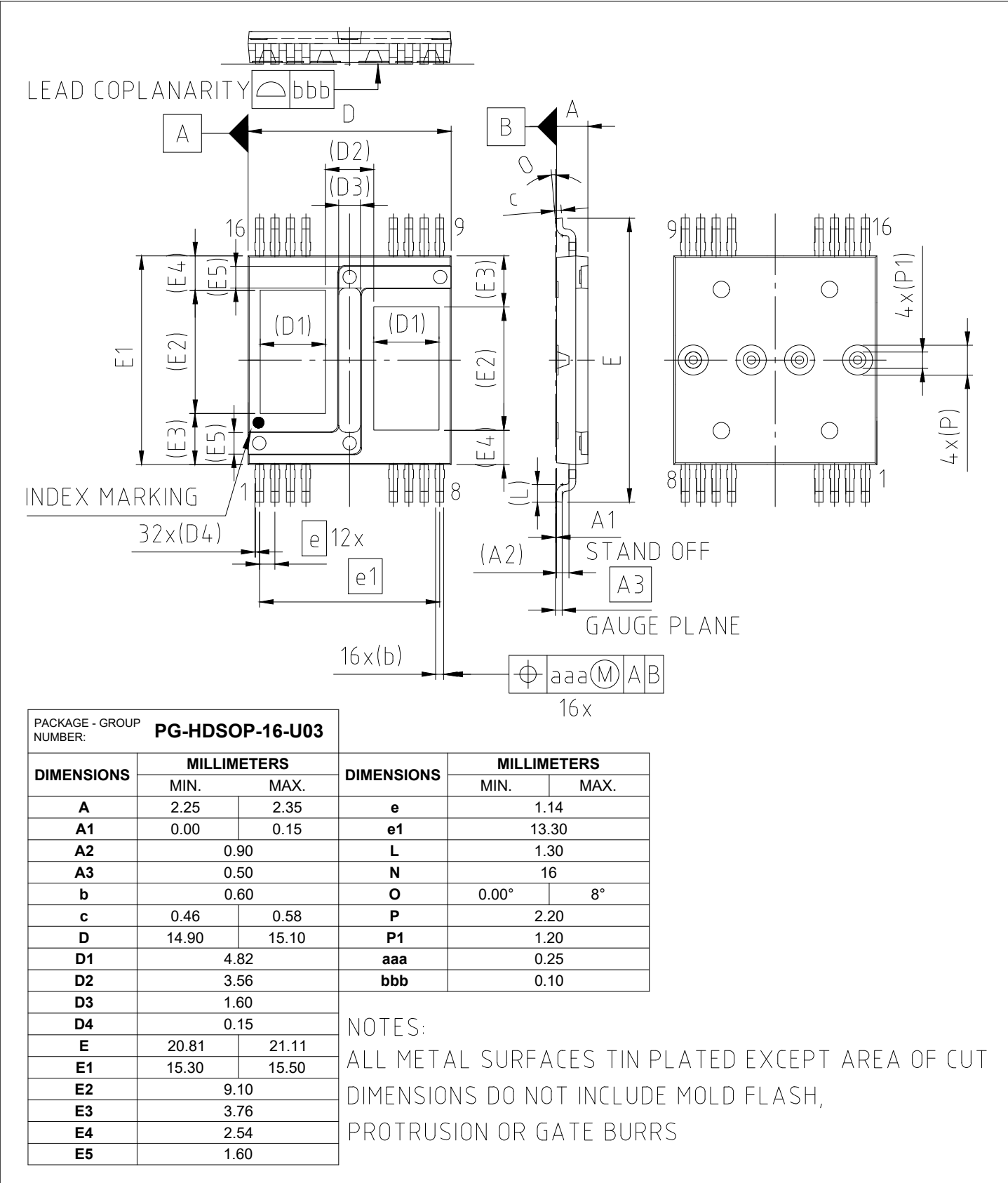


Figure 1

6 Testing conditions

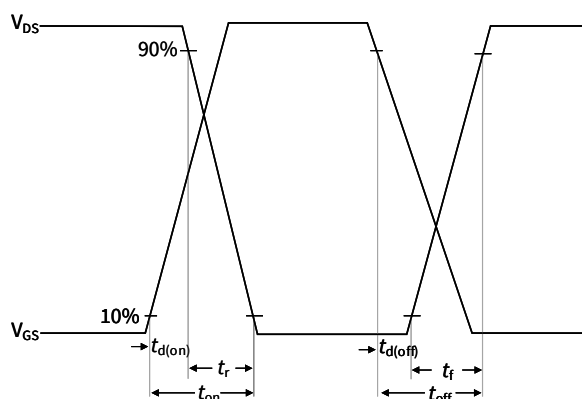


Figure A. Definition of switching times

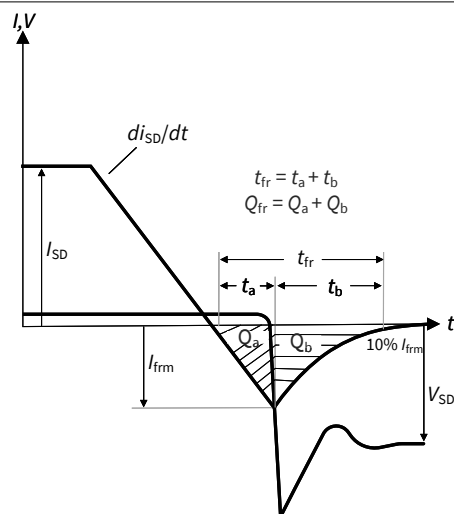


Figure B. Definition of body diode switching characteristics

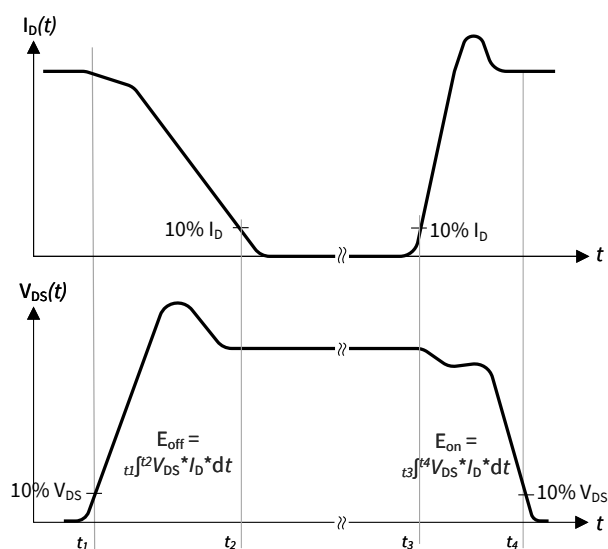


Figure C. Definition of switching losses

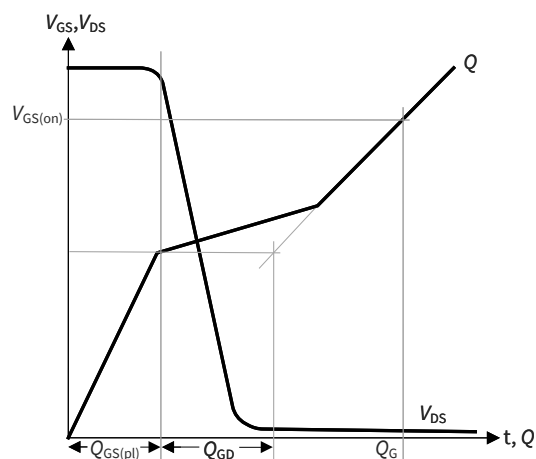


Figure D. Definition of Q_{GD}

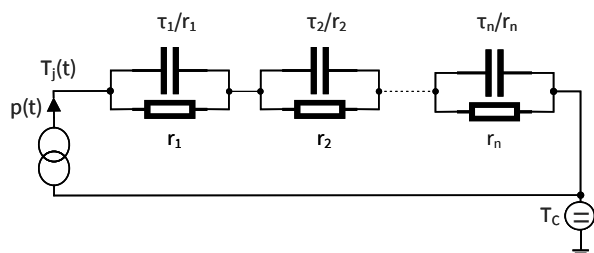


Figure E. Thermal equivalent circuit

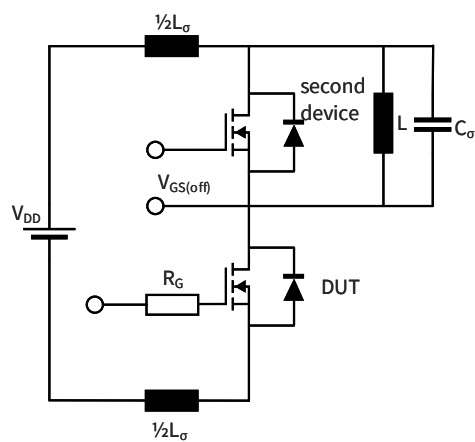


Figure F. Dynamic test circuit

Parasitic inductance L_{σ} ,
Parasitic capacitor C_{σ} ,

Figure 2



Revision history

Revision history

Document revision	Date of release	Description of changes
0.10	2025-11-03	Preliminary datasheet
1.00	2025-11-13	Final datasheet

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